









TPSM83102, TPSM83103 JAJSP72 - AUGUST 2024

TPSM83102 および TPSM83103 1.2A 出力電流、昇降圧モジュール

1 特長

TEXAS

INSTRUMENTS

- 入力電圧範囲:1.6V~5.5V - スタートアップ時のデバイス入力電圧 > 1.65V
- 出力電圧範囲 (調整可能):1V~5.5V
- 高い出力電流能力、3Aピークスイッチ電流
 - V_{IN} ≧ 3V、V_{OUT} = 3.3V 時の出力電流:1.5A
 - V_{IN} ≧ 2.7V、V_{OUT} = 3.3V 時の出力電流: 1.2A
- 全負荷範囲にわたって高効率を実現
 - 静止電流:8µA (代表値)
 - 自動パワー セーブ モードおよび強制 PWM モー ドを構成可能
- ピーク電流昇降圧モードアーキテクチャ
 - シームレスなモード遷移
 - 順方向および逆方向電流動作
 - あらかじめ出力にバイアスを印加した状態で起動
 - 2MHz スイッチングの固定周波数動作
- 安全性と堅牢な動作機能
 - 過電流保護および短絡保護
 - アクティブ ランプを採用したソフト スタート機能内 蔵
 - 過熱保護および過電圧保護
 - 負荷の切り離しを伴う真のシャットダウン機能
 - 順方向および逆方向の電流制限
- 小型ソリューション サイズ
 - 2.6mm × 2.0mm × 1.2mm (最大) 8 ピン µSiP パ ッケージ

2 アプリケーション

- TWS
- システムプリレギュレータ(スマートフォン、タブレット、 端末、テレマティクス)
- ・ ポイントオブロードレギュレーション(有線センサ、ポ ート/ケーブルアダプタ、ドングル)
- 指紋、カメラ センサ (電子スマート ロック、IP ネットワー クカメラ)
- 電圧スタビライザ (データコム、光モジュール、冷却 / 加熱)

3 概要

TPSM83102 および TPSM83103 は、小型 µSiP モジュ ール パッケージに封止された定周波数ピーク電流モード 制御昇降圧コンバータです。3Aのピーク電流制限(標準 値)と1.6V~5.5Vの入力電圧範囲を備え、システムプリ レギュレータと電圧スタビライザの電源ソリューションを提 供します。

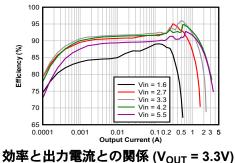
TPSM83102 および TPSM83103 は入力電圧に応じて 自動的に昇圧モード、降圧モード、3 サイクル昇降圧モー ド (入力電圧が出力電圧とほぼ等しい場合) で動作しま す。モード間の遷移は定義されたデューティサイクルで発 生し、モード間の不要な切り替えが避けられるので出力電 圧リップルを減らすことができます。8µAの静止電流とパワ ー セーブ モードの電力により、軽負荷から無負荷までの 状況で最高の効率を実現します。

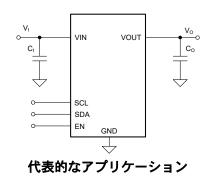
このデバイスは、µSiP モジュール パッケージで非常に小 型のソリューションサイズを実現しています。

パッケージ情報						
部品番号	パッケージ ⁽¹⁾	本体サイズ (公称)				
TPSM83102 ⁽²⁾	µSiP モジュール	2.6mm × 2.0mm × 1.2mm (最大高さ)				
TPSM83103	µSiP モジュール	2.6mm × 2.0mm × 1.2mm (最大高さ)				

供給されているすべてのパッケージについては、セクション 12 を (1) 参照してください。

製品プレビュー詳細は テキサス・インスツルメンツまでお問い合わ (2) せください。





このリソースの元の言語は英語です。翻訳は概要を便宜的に提供するもので、自動化ツール (機械翻訳)を使用していることがあり、TI では翻訳の正確性および妥当 か
性につきましては一切保証いたしません。実際の設計などの前には、ti.com で必ず最新の英語版をご参照くださいますようお願いいたします。





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4 Device Comparison Table

PART NUMBER	Default Setting of Internal EN ⁽²⁾	I2C Slave Address
TPSM83102 ⁽¹⁾	CONVERTER_EN = 0	0x6A
TPSM831021 ⁽¹⁾	CONVERTER_EN = 0	0x68
TPSM831022 ⁽¹⁾	CONVERTER_EN = 0	0x69
TPSM831023 ⁽¹⁾	CONVERTER_EN = 0	0x6B
TPSM83103	CONVERTER_EN = 1	0x6A

(1) Product Preview. Contact TI factory for more information.

(2) Refer to the register map.



5 Pin Configuration and Functions

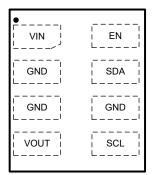


図 5-1. 8-Pin SIU µSiP Module Package (Top View)

表 5-1. Pin Functions

P	IN	I/O ⁽¹⁾	DESCRIPTION
NAME	NO.	1/0(/	DESCRIPTION
VIN	1	PWR	Supply input voltage
GND	2, 3, 6	PWR	Power ground
VOUT	4	PWR	Power stage output
SCL	5	I/O	I2C serial interface clock. Pull this pin up to the I2C bus voltage with a resistor or a current source.
SDA	7	I/O	I2C serial interface data. Pull this pin up to the I2C bus voltage with a resistor or a current source.
EN	8	I	Device enable. Set High to enable and Low to disable. It must not be left floating.

(1) PWR = power, I = input, I/O = input and output



6 Specifications

6.1 Absolute Maximum Ratings

over operating junction temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V	Input voltage (VIN, VOUT, EN, SCL, SDA) ⁽²⁾	-0.3	6.0	V
VI	Input voltage for less than 10 ns	-0.3	7	V
TJ	Operating junction temperature	-40	150	°C
T _{stg}	Storage temperature	-65	150	°C

(1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

(2) All voltage values are with respect to network ground terminal, unless otherwise noted.

6.2 ESD Rating

			VALUE	UNIT	
V	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±1000	V	
V _(ESD)		Charged-device model (CDM), per JEDEC specification JS-002 ⁽²⁾	± 500	v	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating junction temperature (unless otherwise noted)

			MIN	NOM	MAX	UNIT
VI	Supply voltage		1.6		5.5	V
Vo	Output voltage		1.0		5.5	V
CI	Effective Input capacitance	V _I = 1.6 V to 5.5 V	4.2			μF
Co	Effective Output capacitance	1.2 V \leq V _O \leq 3.6 V, nominal value at V _O = 3.3 V	10.4	16.9	330	μF
0		3.6 V < V _O \leq 5.5 V, nominal value at V _O = 5 V	7.95	10.6	330	μF
L	Effective Inductance		0.7	1	1.3	μH
TJ	Operating junction temperature range		-40		125	°C

6.4 Thermal Information

over operating free-air temperature range (unless otherwise noted)

		TPSM83102 TPSM83103	
	THERMAL METRIC	uSiP-SIU	UNIT
		8	
R _{OJA}	Junction-to-ambient thermal resistance	100	°C/W
R _{OJC(top)}	Junction-to-case (top) thermal resistance	42.2	°C/W
R _{OJB}	Junction-to-board thermal resistance	33.2	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	N/A	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	32.2	°C/W
R _{OJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	°C/W

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6.5 Electrical Characteristics

Over operating junction temperature range and recommended supply voltage range (unless otherwise noted). Typical values are at $V_1 = 3.8 \text{ V}$, $V_0 = 3.3 \text{ V}$ and $T_3 = 25^{\circ}\text{C}$ (unless otherwise noted).

		<u> </u>	TEST	CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY								
I _{SD}	Shutdown current into VIN		V _I = 3.8 V, V _(EN) = 0 V	T _{.1} = 25°C		0.5	0.9	μA
IQ	Quiescent current into VIN			$V_1 = 2.2 \text{ V}, V_0 = 3.3 \text{ V}, V_{(EN)} = 2.2 \text{ V}, \text{ no switching}$			6.1	μΑ
	Quiescent current into VOUT	-	$V_1 = 2.2 \text{ V}, V_0 = 3.3 \text{ V}, V_0$			8		μΑ
V _{IT+}	Positive-going UVLO thresho	old voltage			1.5	1.55	1.599	V
V _{IT-}	Negative-going UVLO thresh	•	During start-up		1.4	1.45	1.499	V
V _{hys}	UVLO threshold voltage hyst				99			mV
V _{I(POR)T+}	Positive-going POR threshol		maximum of V _I or V _O		1.25	1.45	1.65	V
V _{I(POR)T-}	Negative-going POR thresho	_			1.22	1.43	1.6	V
I/O SIGNAL								
V _{T+}	Positive-going threshold voltage	EN, MODE			0.77	0.98	1.2	V
V _{T-}	Negative-going threshold voltage	EN, MODE			0.5	0.66	0.76	V
V _{hys}	Hysteresis voltage	EN, MODE				300		mV
I _{IH}	High-level input current	(EN, MODE)	$V_{(EN)} = V_{(MODE)} = 1.5 V,$ no pullup resistor			±0.01	±0.25	μA
IIL	Low-level input current	(EN, MODE)	$V_{(EN)} = V_{(MODE)} = 0 V,$	$V_{(EN)} = V_{(MODE)} = 0 V,$		±0.01	±0.1	μA
	Input bias current	(EN, MODE)	V _(EN) = 5.5 V	V _(EN) = 5.5 V		±0.01	±0.3	μA
POWER SV	МІТСН							
		Q1				45		mΩ
_		Q2	V _I = 3.8 V, V _O = 3.3 V,			50		mΩ
r _{DS(on)}	On-state resistance	Q3	test current = 0.2 A			50		mΩ
		Q4				85		mΩ
CURRENT	LIMIT	1	1		1			
I _{L(PEAK)}	Switch peak current limit ⁽¹⁾	Q1	Vin=3.8V, V _O = 3.3 V	Output sourcing current	2.6	3	3.35	А
	PFM mode entry threshold (p	beak) current	I _O falling			145		mA
OUTPUT							I	
CONTROL	[FEEDBACK PIN]							
PROTECTI	ON FEATURES							
V _{T+(OVP)}	Positive-going OVP threshold voltage	d			5.55	5.75	5.95	V
V _{T+(IVP)}	Positive-going IVP threshold voltage				5.55	5.75	5.95	V
TIMING PA	RAMETERS						1	
t _{d(EN)}	Delay between a rising edge and the start of the output vo	on the EN pin Itage ramp				0.87	1.5	ms
t _{d(ramp)}	Soft-start ramp time				6.42	7.55	8.68	ms
f _{SW}	Switching frequency				1.8	2	2.2	MHz

(1) Current limit production test are performed under DC conditions. The current limit in operation is somewhat higher and depending on propagation delay and the applied external components

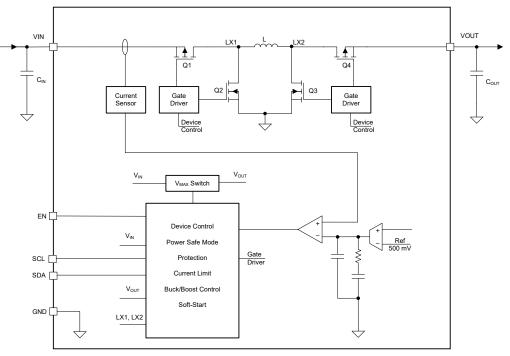


7 Detailed Description

7.1 Overview

The TPSM83102 and TPSM83103 is a constant frequency peak current mode control buck-boost converter. The converter uses a fixed-frequency topology with approximately 2-MHz switching frequency. The modulation scheme has three clearly defined operation modes where the converters enter with defined thresholds over the full operation range of V_{IN} and V_{OUT} . The maximum output current is determined by the Q1 peak current limit, which is typically 3 A.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Undervoltage Lockout (UVLO)

The input voltage of the VIN pin is continuously monitored if the device is not in shutdown mode. UVLO only stops or starts the converter operation. The UVLO does not impact the core logic of the device. UVLO avoids a brownout of the device during device operation. In case the supply voltage on the VIN pin is lower that the negative-going threshold of UVLO, the converter stops its operation. To avoid a false disturbance of the power conversion, the UVLO falling threshold logic signal is digitally de-glitched.

If the supply voltage on the VIN pin recovers to be higher than the UVLO rising threshold, the converter returns to operation. In this case, the soft-start procedure restarts faster than under start-up without a pre-biased output.



7.3.2 Enable and Soft Start

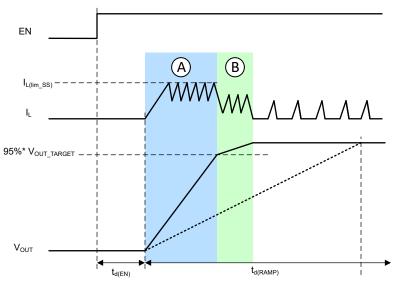


図 7-1. Typical Soft-Start Behavior

When the input voltage is above the UVLO rising threshold and the EN pin is pulled to a voltage above 1.2 V, the TPSM83102 and TPSM83103 are enabled and start up after a short delay time, $t_{d(EN)}$.

The devices have an inductor peak current clamp to limit the inrush current during start-up. When the minimum current clamp $(I_{L(lim_SS)})$ is lower than the current that is necessary to follow the voltage ramp, the current automatically increases to follow the voltage ramp. The minimum current limit ensures as fast as possible soft start if the capacitance is chosen lower than what the ramp time $t_{d(RAMP)}$ was selected for.

In a typical start-up case as shown in \boxtimes 7-1 (low output load, typical output capacitance), the minimum current clamp limits the inrush current and charges the output capacitor. The output voltage then rises faster than the reference voltage ramp (see phase A in \boxtimes 7-1). To avoid an output overshoot, the current clamp is deactivated when the output is close to the target voltage and follows the reference voltage ramp slew value given by the voltage ramp, which is finishing the start up (see phase B in \boxtimes 7-1). The transition from the minimum current clamp operation is sensed by using the threshold 95% Vout_target. After phase B, the output voltage is well regulated to the nominal target voltage. The current waveform depends on the output load and operation mode.

7.3.3 Adjustable Output Voltage

The output voltage is adjusted by the I2C control. Please refer to the part of "Programming" and "Register Map" for the Vout settings.

7.3.4 Reverse Current Operation

The device can support reverse current operation in FPWM mode(the current flows from VOUT pin to VIN pin). If the output feedback voltage on the FB pin is higher than the reference voltage, the converter regulation forces a current into the input capacitor. The reverse current operation is independent of the V_{IN} voltage or V_{OUT} voltage ratio, hence it is possible on all device operation modes boost, buck, or buck-boost.

7.3.5 Protection Features

The following sections describe the protection features of the device.

7.3.5.1 Input Overvoltage Protection

The TPSM83102 and TPSM83103 have input overvoltage protection which avoids any damage to the device in case the current flows from the output to the input and the input source cannot sink current (for example, a diode in the supply path).



If forced PWM mode is active, the current can go negative until it reaches the sink current limit. Once the input voltage threshold, $V_{T+(IVP)}$, is reached on the VIN pin, the protection disables forced PWM mode and only allows current to flow from VIN to VOUT. After the input voltage drops under the input voltage protection threshold, forced PWM mode can be activated again.

7.3.5.2 Short Circuit Protection

The device features peak current limit performance at short circuit protection. \boxtimes 7-2 shows a typical device behavior of an short/overload event of the short circuit protection.

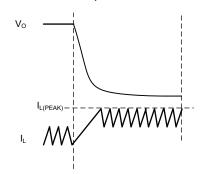


図 7-2. Typical Device Behavior During Short Circuit Protection

7.3.5.3 Thermal Shutdown

To avoid thermal damage of the device, the temperature of the die is monitored. The device stops operation once the sensed temperature rises over the thermal threshold. After the temperature drops below the thermal shutdown hysteresis, the converter returns to normal operation.

7.4 Device Functional Modes

The device has two functional modes: off and on. The device enters the on mode when the voltage on the VIN pin is higher than the UVLO threshold and a high logic level is applied to the EN pin. The device enters the off mode when the voltage on the VIN pin is lower than the UVLO threshold or a low logic level is applied to the EN pin.

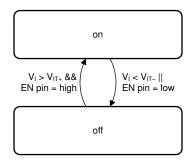


図 7-3. Device Functional Modes

7.5 Programming

7.5.1 Serial Interface Description

 I^2C is a 2-wire serial interface developed by Philips Semiconductor, now NXP Semiconductors (see *NXP Semiconductors, UM10204 – I²C-Bus Specification and User Manual*). The bus consists of a data line (SDA) and a clock line (SCL) with pullup structures. When the bus is idle, both SDA and SCL lines are pulled high. All the I²C-compatible devices connect to the I²C bus through open-drain I/O pins, SDA, and SCL. A master device, usually a microcontroller or a digital signal processor, controls the bus. The master is responsible for generating the SCL signal and device addresses. The master also generates specific conditions that indicate the START

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and STOP of data transfer. A slave device receives and transmits data on the bus under control of the master device.

The device works as a slave and supports the following data transfer modes, as defined in the I²C-Bus Specification:

- Standard-mode (100 kbps)
- Fast-mode (400 kbps)
- Fast-mode Plus (1 Mbps)

The interface adds flexibility to the power supply solution, enabling most functions to be programmed to new values, depending on the instantaneous application requirements. Register contents remain intact as long as supply voltage remains above $V_{\text{IT+(POR)}}$.

The data transfer protocol for standard and fast modes is exactly the same, therefore, it is referred to as F/S-mode in this document. The device supports 7-bit addressing; 10-bit addressing and general call address are not supported. The device 7-bit address is 6Ah (01101010b).

To make sure that the I²C function in the device is correctly reset, it is recommended that the I²C master initiates a STOP condition on the I²C bus after the initial power up of SDA and SCL pullup voltages.

7.5.2 Standard-, Fast-, and Fast-Mode Plus Protocol

The master initiates a data transfer by generating a start condition. The start condition is when a high-to-low transition occurs on the SDA line while SCL is high, as shown in \boxtimes 7-4. All I²C-compatible devices recognize a start condition.

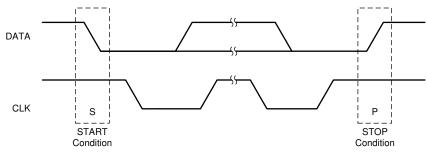


図 7-4. START and STOP Conditions

The master then generates the SCL pulses and transmits the 7-bit address and the read/write direction bit, R/W, on the SDA line. During all transmissions, the master ensures that data is valid. A valid data condition requires the SDA line to be stable during the entire high period of the clock pulse (see \boxtimes 7-5). All devices recognize the address sent by the master and compare it to their internal fixed addresses. Only the slave device with a matching address generates an acknowledge (see \boxtimes 7-6) by pulling the SDA line low during the entire high period of the ninth SCL cycle. Upon detecting this acknowledge, the master knows that communication link with a slave has been established.

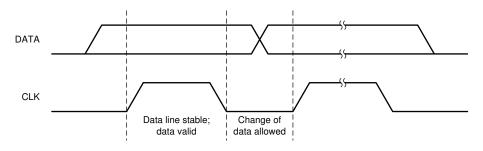


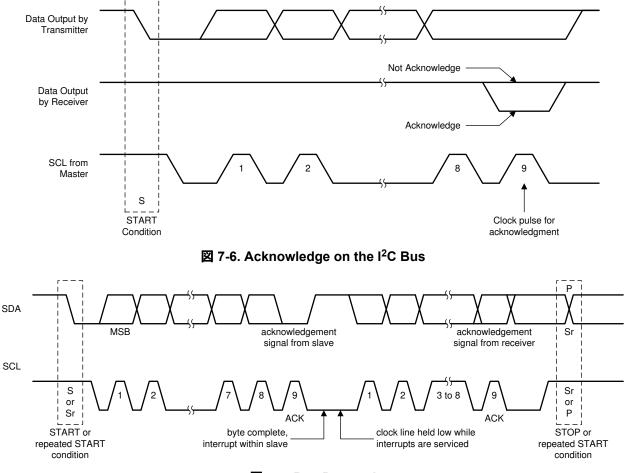
図 7-5. Bit Transfer on the Serial Interface



The master generates further SCL cycles to either transmit data to the slave (R/W bit 1) or receive data from the slave (R/W bit 0). In either case, the receiver needs to acknowledge the data sent by the transmitter. An acknowledge signal can either be generated by the master or by the slave, depending on which one is the receiver. 9-bit valid data sequences consisting of 8-bit data and 1-bit acknowledge can continue as long as necessary.

To signal the end of the data transfer, the master generates a stop condition by pulling the SDA line from low to high while the SCL line is high (see \boxtimes 7-4). This releases the bus and stops the communication link with the addressed slave. All I²C-compatible devices must recognize the stop condition. Upon the receipt of a stop condition, all devices know that the bus is released and they wait for a start condition followed by a matching address.

Attempting to read data from register addresses not listed in this section results in 00h being read out.



🛛 7-7. Bus Protocol

7.5.3 I²C Update Sequence

A single update requires the following:

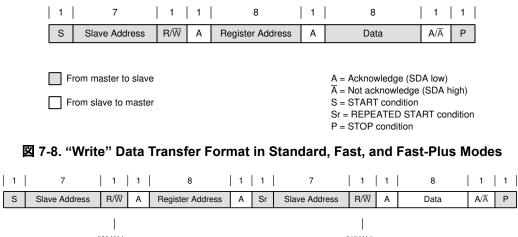
- A start condition
- A valid I²C slave address
- A register address
- A data byte

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To acknowledge the receipt of each byte, the device pulls the SDA line low during the high period of a single clock pulse. The device performs an update on the falling edge of the acknowledge signal that follows the last byte.







7.6 Register Map

7.6.1 Register Description

7.6.1.1 Register Map

表 7-1. Register Map						
ADDRESS	SECTION					
0x02	CONTROL1	Control 1 Register	Go			
0x03	VOUT	VOUT Register	Go			
0x05	CONTROL2	Control 2 Register	Go			

7.6.1.2 Register CONTROL1 (Register address: 0x02; Default: 0x08)

Return to Register Map

表 7-2. Register CONTROL1 Format

7	6	5	4	3	2	1	0			
NIL[3:0]			NIL	EN_SCP	NIL	CONVERTER_EN				
R			R	R/W	R	R/W				

LEGEND: R/W = Read/Write; R = Read only

SCP: Short Circuit Protection

Bit	Field	Туре	Reset	Description
7:4	NIL	R	060000	Not used. During write operations data for these bits are ignored. During read operations 0 is returned
3	EN_FAST_DVS	R/W	0b1	Sets DVS to fast mode 0 : DISABLE, 1 : ENABLE
2	EN_SCP	R/W	0b0	Enable short circuit hiccup protection 0 : DISABLE, 1 : ENABLE
1	NIL	R	0b0	Not used.
0	CONVERTER_EN	R/W	0b0	Enable Converter ('AND'ed with EN-pin) 0 : DISABLE, 1 : ENABLE

表 7-3. Register CONTROL1 Field Descriptions

7.6.1.3 Register VOUT (Register address: 0x03; Default: 0x5C)

Return to Register Map

	表 7-4. Register VOUT Format											
7	7 6 5 4 3 2 1 0											
			VOUT	T[7 :0]								
			R	W								

LEGEND: R/W = Read/Write

表 7-5. Register VOUT Field Descriptions

Bit	Field	Туре	Reset	Description				
7:0 VOUT[7:0] R/W 0x5C		0x5C	These bits set the output voltage					
				Output voltage = 1.000 + (VOUT[7 :0] × 0.025) V when 0x00<=VOUT[7 :0]<=0xB4;				
				Output voltage = 5.5 V when 0xB5<=VOUT[7 :0]<=0xFF				

7.6.1.4 Register CONTROL2 (Register address: 0x05; Default: 0x45)

Return to Register Map

表 7-6. Register CONTROL2 Format

7	6	5 4		3	2 1 0				
FPWM	FAST_RAMP_E N	EN_DISCH	_VOUT[1:0]	CL_RAMP_MIN		TD_RAMP[2:0]			
R/W	R/W	R/	W	R/W		R/W			

LEGEND: R/W = Read/Write

表 7-7. Register CONTROL2 Field Descriptions

Bit	Field	Туре	Reset	Description	
7	FPWM		0b0	Force PWM operation 0 : DISABLE, 1 : ENABLE	
6	FAST_RAMP_EN	R/W	0b1	Device can start-up faster then VOUT ramp 0 : DISABLE, 1 : ENABLE	



Bit	Field	Туре	Reset	Description
5:4	EN_DISCH_VOUT[1:0]	R/W	0Ь00	Enable of BUBO Vout Discharge 00 : DISABLE 01 : SLOW (34mA) 10 : MEDIUM (67mA) 11 : FAST (100mA)
3	CL_RAMP_MIN	R/W	060	Define the minimum current limit during the soft start ramp 0 : Low (500mA) 1 : High (2x Low)
2:0	TD_RAMP[2:0]	R/W	0b101	Defines the ramp time for the Vo soft start ramp 000: 0.256ms 001: 0.512ms 010: 1.024ms 011: 1.920ms 100: 3.584ms 101: 7.552ms 110: 9.600ms 111: 24.320ms

表 7-7. Register CONTROL2 Field Descriptions (続き)



8 Application and Implementation

注

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8.1 Application Information

The TPSM83102 and TPSM83103 are a high-efficiency, low-quiescent current, buck-boost modules. The devices are suitable for applications needing a regulated output voltage from an input supply that can be higher or lower than the output voltage. The output voltage can be set from 1.0V to 5.5V conveniently by I2C.

8.2 Typical Application

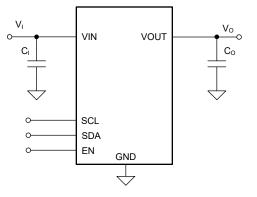


図 8-1. 3.3-V_{OUT} Typical Application

8.2.1 Design Requirements

The design parameters are listed in \pm 8-1.

表 8-1. Design Parameters

PARAMETERS	VALUES				
Input voltage	2.7 V to 4.3 V				
Output voltage	3.3 V				
Output current	1.5 A				

8.2.2 Detailed Design Procedure

The first step is the selection of the output filter components. To simplify this process, 222×6.3 outlines minimum and maximum values for capacitance. Pay attention to the tolerance and derating when selecting nominal capacitance.

8.2.2.1 Custom Design with WEBENCH Tools

Click here to create a custom design using the TPSM83102 and TPSM83103 devices with the WEBENCH[®] Power Designer.

- 1. Start by entering your V_{IN}, V_{OUT} and I_{OUT} requirements.
- 2. Optimize your design for key parameters like efficiency, footprint or cost using the optimizer dial and compare this design with other possible solutions from Texas Instruments.
- 3. WEBENCH Power Designer provides you with a customized schematic along with a list of materials with real time pricing and component availability.
- 4. In most cases, you can:



- Run electrical simulations to see important waveforms and circuit performance,
- · Run thermal simulations to understand the thermal performance of your board,
- · Export your customized schematic and layout into popular CAD formats,
- Print PDF reports for the design, and share your design with colleagues.
- 5. Get more information about WEBENCH tools at www.ti.com/webench.

8.2.2.2 Output Capacitor Selection

For the output capacitor, use small ceramic capacitors placed as close as possible to the VOUT and PGND pins of the IC. The recommended nominal output capacitor value is a single 47 μ F. If, for any reason, the application requires the use of large capacitors that cannot be placed close to the IC, use a smaller ceramic capacitor in parallel to the large capacitor. and place the small capacitor as close as possible to the VOUT and PGND pins of the module.

It is important that the effective capacitance is given according to the recommended value in $\forall 2 \neq 2 \neq 2 > 6.3$. In general, consider DC bias effects resulting in less effective capacitance. The choice of the output capacitance is mainly a tradeoff between size and transient behavior as higher capacitance reduces transient response over/ undershoot and increases transient response time. Possible output capacitors are listed in $\frac{1}{5}$ 8-2.

CAPACITOR VALUE [µF]	VOLTAGE RATING [V]	ESR [mΩ]	PART NUMBER	MANUFACTURER ⁽¹⁾	SIZE (METRIC)	
47	6.3	10	GRM219R60J476ME44	Murata	0805 (2012)	
47	10	40	CL10A476MQ8QRN	Semco	0603 (1608)	

表 8-2. List of Recommended Capacitors

(1) See the セクション 10.1.1.

8.2.2.3 Input Capacitor Selection

A 22- μ F input capacitor is recommended to improve line transient behavior of the regulator and EMI behavior of the total power supply circuit. An X5R or X7R ceramic capacitor placed as close as possible to the VIN and PGND pins of the module is recommended. This capacitance can be increased without limit. If the input supply is located more than a few inches from the TPSM83102 or TPSM83103, additional bulk capacitance can be required in addition to the ceramic bypass capacitors. An electrolytic or tantalum capacitor with a value of 47 μ F is a typical choice.

表 8-3. List of Recommended Capacitors

CAPACITOR VALUE [µF]	VOLTAGE RATING [V]	ESR [mΩ]	PART NUMBER	MANUFACTURER ⁽¹⁾	SIZE (METRIC)
22	6.3	43	GRM187R61A226ME15	Murata	0603 (1608)
10	10	40	GRM188R61A106ME69	Murata	0603 (1608)

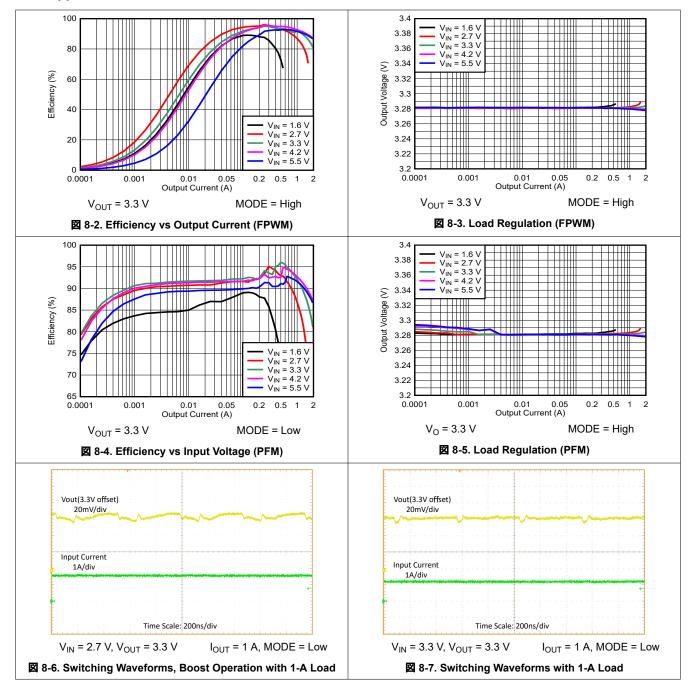
(1) See the セクション 10.1.1.

8.2.2.4 Setting the Output Voltage

The output voltage is set by I2C. Please refer to the part of "Register Vout" for the detailed output voltage settings.



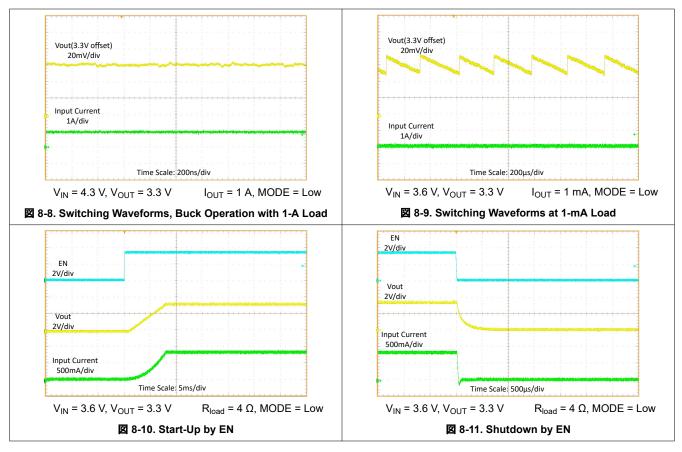
8.2.3 Application Curves



TPSM83102, TPSM83103 JAJSP72 – AUGUST 2024

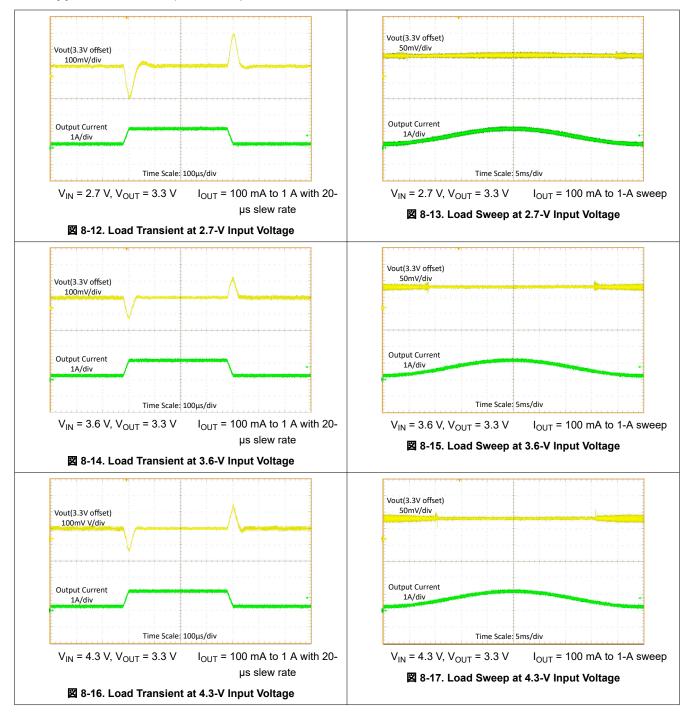


8.2.3 Application Curves (continued)





8.2.3 Application Curves (continued)





8.2.3 Application Curves (continued)

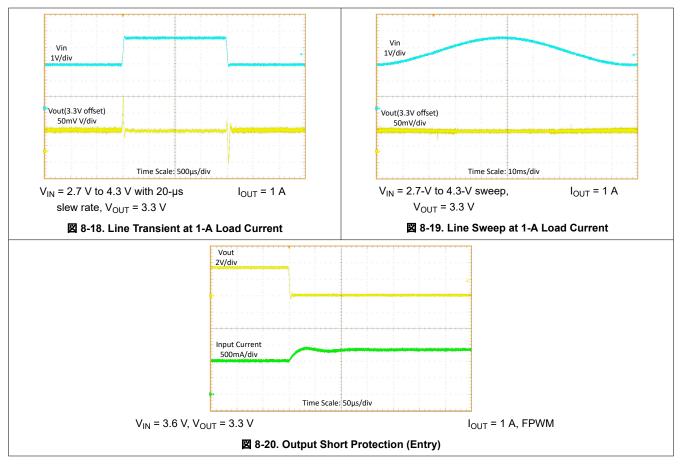


表 8-4. Components for Application Characteristic Curves for V_{OUT} = 3.3 V

REFERENCE	DESCRIPTION	PART NUMBER	MANUFACTURER ⁽¹⁾	
U1	High Power Density 1.5 A Buck-Boost Converter	TPSM83102 or TPSM83103	Texas Instruments	
C1	22 $\mu\text{F},$ 0603, Ceramic Capacitor, ±20%, 6.3 V	GRM187R61A226ME15	Murata	
C2	47 $\mu\text{F},$ 0805, Ceramic Capacitor, ±20%, 6.3 V	GRM219R60J476ME44	Murata	

(1) See the セクション 10.1.1.



9 Layout

9.1 Layout Guidelines

The PCB layout is an important step to maintain the high performance of the TPSM83102 and TPSM83103 devices.

• Place input and output capacitors as close as possible to the IC. Traces need to be kept short. Route wide and direct traces to the input and output capacitors results in low trace resistance and low parasitic inductance.

9.2 Layout Example

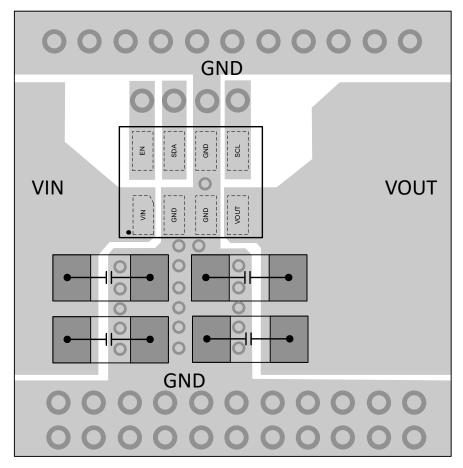


図 9-1. Layout Example



10 Device and Documentation Support

10.1 Device Support

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10.1.2 Development Support

10.1.2.1 Custom Design with WEBENCH Tools

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- 2. Optimize your design for key parameters like efficiency, footprint or cost using the optimizer dial and compare this design with other possible solutions from Texas Instruments.
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 - Run electrical simulations to see important waveforms and circuit performance,
 - Run thermal simulations to understand the thermal performance of your board,
 - Export your customized schematic and layout into popular CAD formats,
 - Print PDF reports for the design, and share your design with colleagues.
- 5. Get more information about WEBENCH tools at www.ti.com/webench.

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10.6 用語集

テキサス・インスツルメンツ用語集 この用語集には、用語や略語の一覧および定義が記載されています。



11 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

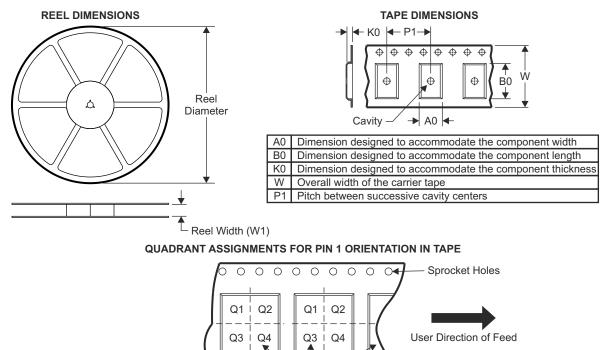
DATE	REVISION	NOTES
August 2024	*	Initial Release



12 Mechanical, Packaging, and Orderable Information

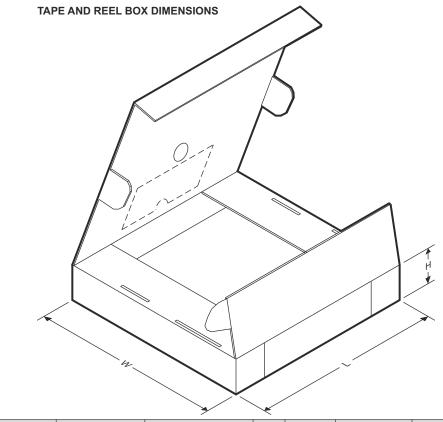
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

12.1 Tape and Reel Information



Pocket Quadrants												
DevicePackage TypePackage DrawingPinsSPQReel Diameter (mm)Reel Width W1 (mm)A0 (mm)B0 (mm)K0 (mm)P1 (mm)W Pint Quadrant										Pin1 Quadrant		
TPSM83103SIUR	μSiP	SIU	8	3000	330	12.4	2.3	2.9	1.35	8	12	Q1





Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPSM83103SIUR	μSiP	SIU	8	3000	383	353	58



SIU0008A

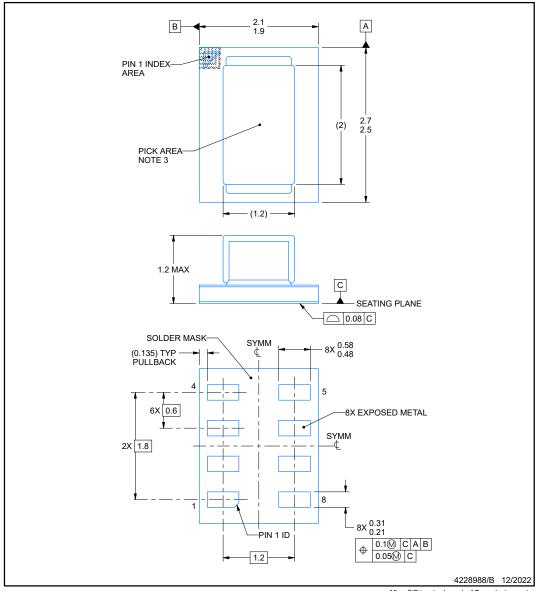




PACKAGE OUTLINE

MicroSiP[™] - 1.2 mm max height

MICRO SYSTEM IN PACKAGE



NOTES:

MicroSiP is a trademark of Texas Instruments

All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 Pick and place nozzle Ø 0.33 mm or smaller recommended.



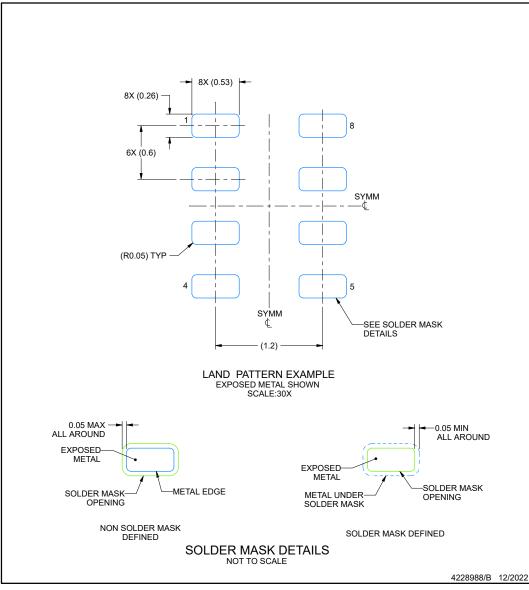


SIU0008A

EXAMPLE BOARD LAYOUT

MicroSiP[™] - 1.2 mm max height

MICRO SYSTEM IN PACKAGE



NOTES: (continued)

4. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



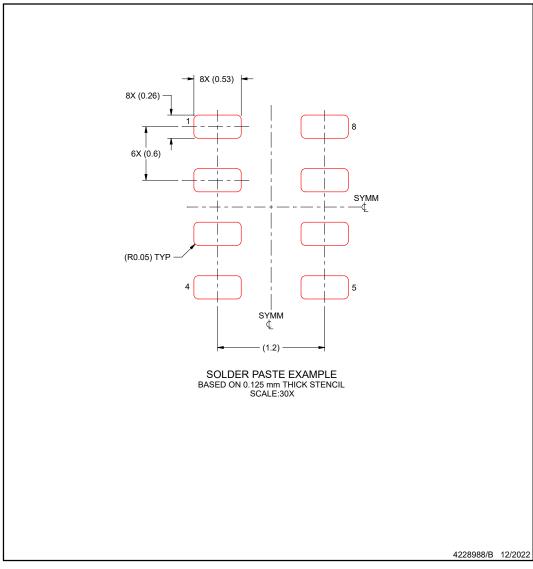
SIU0008A



EXAMPLE STENCIL DESIGN

MicroSiP[™] - 1.2 mm max height

MICRO SYSTEM IN PACKAGE



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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PACKAGING INFORMATION

Orderable Device	Status	Package Type	•	Pins	Package	Eco Plan	Lead finish/	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	Ball material	(3)		(4/5)	
							(6)				
TPSM831021SIUR	ACTIVE	uSiP	SIU	8	3000	RoHS & Green	ENEPIG	Level-2-260C-1 YEAR	-40 to 125	318P HYBM831021	Samples
TPSM831022SIUR	ACTIVE	uSiP	SIU	8	3000	RoHS & Green	ENEPIG	Level-2-260C-1 YEAR	-40 to 125	319P HYBM831022	Samples
TPSM831023SIUR	ACTIVE	uSiP	SIU	8	3000	RoHS & Green	ENEPIG	Level-2-260C-1 YEAR	-40 to 125	3IAP HYBM831023	Samples
TPSM83102SIUR	ACTIVE	uSiP	SIU	8	3000	RoHS & Green	ENEPIG	Level-2-260C-1 YEAR	-40 to 125	3EGL HYBM83102	Samples
TPSM83103SIUR	ACTIVE	uSiP	SIU	8	3000	RoHS & Green	ENEPIG	Level-2-260C-1 YEAR	-40 to 125	3EHL HYBM83103	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

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⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



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